Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Trench MOSFET technology
- · Side wettable flanks for optical solder inspection
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- · AEC-Q101 qualified

3. Applications

- · Relay driver
- · High-speed line driver
- High-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-30	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-	-4.7	Α
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = -10 V; I_D = -4.7 A; T_j = 25 °C		-	40	50	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	1 6	D
2	D	drain		
3	G	gate	2 5	G P
4	S	source	3 8 94	S
5	D	drain	Transparent top view	017aaa257
6	D	drain	DFN2020MD-6 (SOT1220)	
7	D	drain		
8	S	source		

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMPB48EPA	DFN2020MD-6	DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMPB48EPA	4Q

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-30	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-4.7	Α
		V _{GS} = -10 V; T _{amb} = 100 °C	[1]	-	-3	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-19	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[1]	-	1.7	W
		T _{sp} = 25 °C		-	12.5	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain di	ode					
I _S	source current	T _{amb} = 25 °C	[1]	-	-1.8	Α
ESD maximum	rating					
V_{ESD}	electrostatic discharge voltage	НВМ	[2]	-	500	V
Avalanche rugg	jedness		·			
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = -1.1 A; DUT in avalanche (unclamped)		-	17.3	mJ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

^[2] Measured between all pins.

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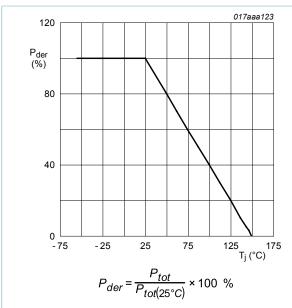


Fig. 1. Normalized total power dissipation as a function of junction temperature

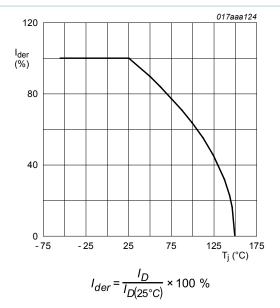
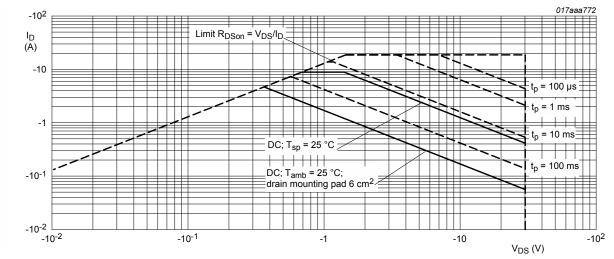


Fig. 2. Normalized continuous drain current as a function of junction temperature



I_{DM} = single pulse

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

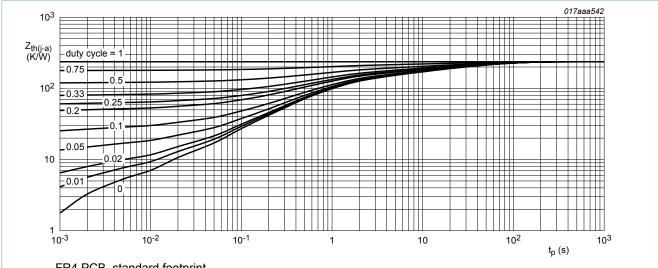
30 V, P-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

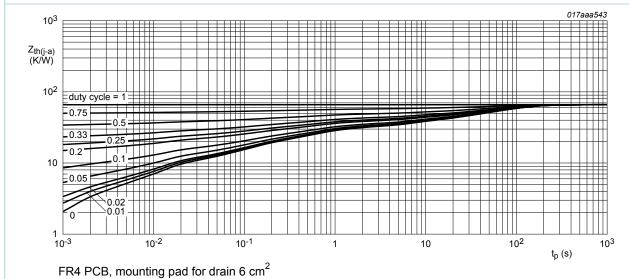
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance		[1]	-	235	270	K/W
	from junction to ambient		[2]	-	67	74	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	5	10	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 5.

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					,
V _{(BR)DSS}	drain-source breakdown voltage	I_D = -250 μ A; V_{GS} = 0 V; T_j = 25 °C	-30	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = -250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C	-1	-1.5	-2.5	V
I _{DSS}	drain leakage current	$V_{DS} = -30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μA
I _{GSS}	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-100	nA
		V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	V_{GS} = -10 V; I_D = -4.7 A; T_j = 25 °C	-	40	50	mΩ
re	resistance	V _{GS} = -10 V; I _D = -4.7 A; T _j = 150 °C	-	60	75	mΩ
		V_{GS} = -4.5 V; I_D = -3.9 A; T_j = 25 °C	-	55	76	mΩ
9 _{fs}	forward transconductance	V_{DS} = -10 V; I_D = -4.7 A; T_j = 25 °C	-	15	-	S
R _G	gate resistance	f = 1 MHz	-	6	-	Ω
Dynamic ch	naracteristics				-	
Q _{G(tot)}	total gate charge	V_{DS} = -15 V; I_{D} = -4.7 A; V_{GS} = -10 V;	-	17	26	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	2.5	-	nC
Q_{GD}	gate-drain charge		-	3.2	-	nC
C _{iss}	input capacitance	V _{DS} = -15 V; f = 1 MHz; V _{GS} = 0 V;	-	860	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	105	-	pF
C _{rss}	reverse transfer capacitance		-	87	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -15 V; I_{D} = -4.7 A; V_{GS} = -10 V;	-	7.4	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	17.5	-	ns
t _{d(off)}	turn-off delay time		-	27	-	ns
t _f	fall time		-	10.4	-	ns
Source-dra	in diode		,			
V_{SD}	source-drain voltage	$I_S = -1.8 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-0.8	-1.2	V
t _{rr}	reverse recovery time	$I_S = -1.8 \text{ A}; dI_S/dt = 100 \text{ A/}\mu\text{s};$	-	11	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = -15 \text{ V}; T_j = 25 \text{ °C}$	-	4	-	nC

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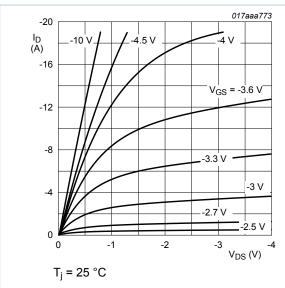


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

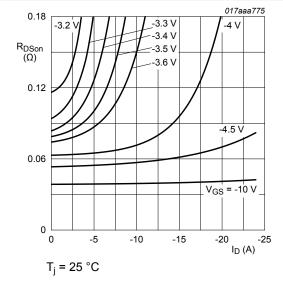


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

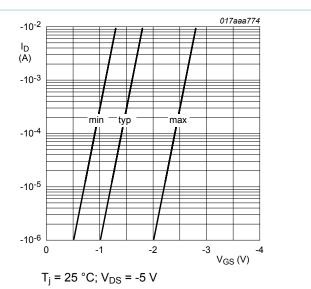


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

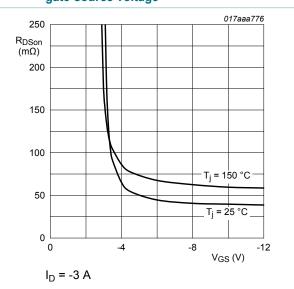


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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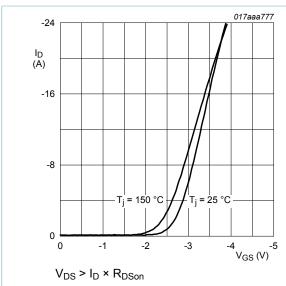


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

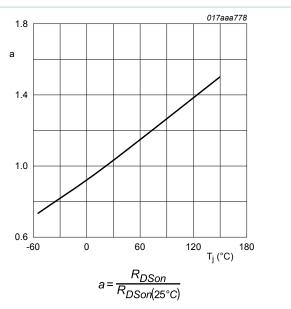


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

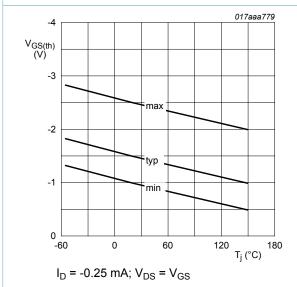


Fig. 12. Gate-source threshold voltage as a function of junction temperature

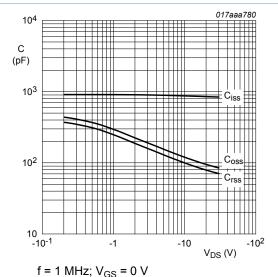


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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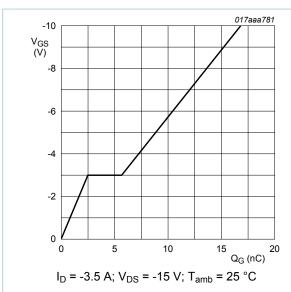


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$

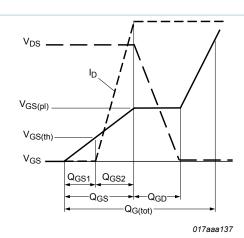


Fig. 15. Gate charge waveform definitions

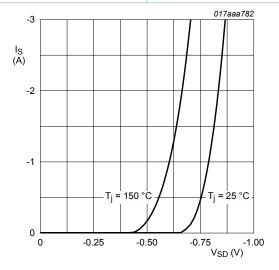
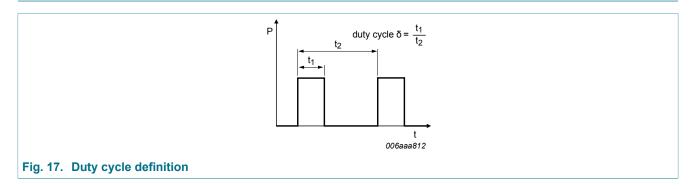


Fig. 16. Source current as a function of source-drain voltage; typical values

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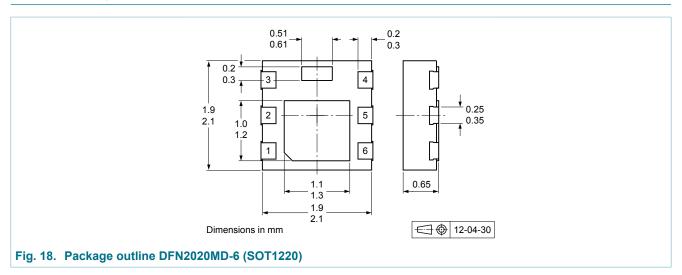
11. Test information



Quality information

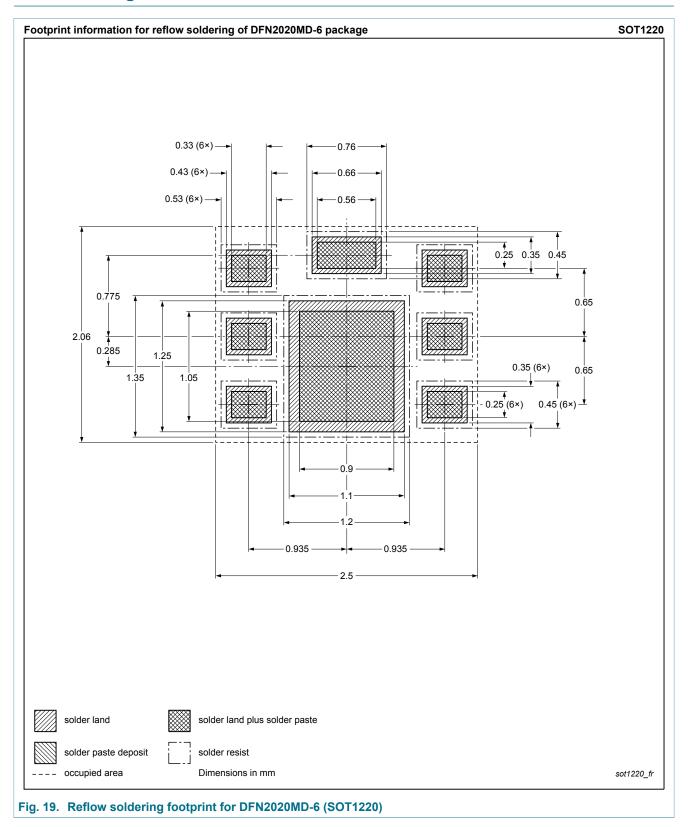
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB48EPA v.1	20180327	Product data sheet	-	-

30 V, P-channel Trench MOSFET

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: <u>org@eplast1.ru</u>

Адрес: 198099, г. Санкт-Петербург, ул. Калинина,

дом 2, корпус 4, литера А.